

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage	V _{CES}	650	V	
Gate-Emitter Voltage	V _{GES}	±20	V	
Transient Gate-emitter voltage (t _p < 5 ms)		±25	V	
Continuous Collector Current	I _C	T _C =25°C	8	A
		T _C =100°C	4	A
Collector Current Pulsed (Note 1)	I _{CM}	16	A	
Diode Forward Current	I _F	T _C =25°C	8	A
		T _C =100°C	4	A
Short Circuit Withstand Time V _{GE} = 15V, V _{CC} ≤ 200V Allowed number of short circuits < 1000 Time between short circuits: ≥ 1.0s T _{VJ} = 25°C	t _{SC}	8	μs	
Power Dissipation (T _C =25°C)	P _D	37	W	
Operating Junction Temperature	T _J	-40 ~ +150	°C	
Storage Temperature Range	T _{STG}	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 Absolute maximum ratings are those values beyond which the device could be permanently damaged.
 2. Pulse width limited by maximum junction temperature.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θ _{JC}	3.37	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Off Characteristics							
Collector-Emitter Breakdown Voltage	BV _{CES}	I _C =250μA, V _{GE} =0V	650			V	
Collector Cut-Off Current	I _{CES}	V _{CE} =650V, V _{GE} =0V			5	μA	
G-E Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} =±20V			±10	μA	
On Characteristics							
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =250μA, V _{CE} =V _{GE}	4.5		7.5	V	
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =4.0A, V _{GE} =15V	T _C =25°C	1.9	2.4	V	
			T _C =125°C	2.3		V	
Dynamic Characteristics							
Input Capacitance	C _{IES}	V _{CE} =25V, V _{GE} =0V, f=1MHz		147		pF	
Output Capacitance	C _{OES}			29		pF	
Reverse Transfer Capacitance	C _{RES}			8		pF	
Switching Characteristics							
Total Gate Charge	Q _G	V _{CE} =520V, I _C =4.0A, V _{GE} =15V		25		nC	
Gate-Emitter Charge	Q _{GE}			14		nC	
Gate-Collector Charge	Q _{GC}			6		nC	
Turn-On Delay Time	t _{DON)}	V _{CC} =400V, I _C =4.0A, R _G =25Ω, V _{GE} =0~15V, L=500μH		2		ns	
Rise Time	t _R			11		ns	
Turn-Off Delay Time	t _{DOFF)}			2		ns	
Fall Time	t _F			218		ns	
Turn-On Switching Loss	E _{ON}			0.17		mJ	
Turn-Off Switching Loss	E _{OFF}			0.11		mJ	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Forward Voltage Drop	V _F		I _F =4.0A			2.0	V
Reverse Recovery Time	t _{rr}	I _F =4.0A, di/dt=100A/μS, V _{CC} =400V		54		ns	
Reverse Recovery Charge	Q _{rr}			146		nC	

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